


## PROTECTIVE ARRANGEMENT FOR A SEMICONDUCTOR CIRCUIT SYSTEM HAVING A THYRISTOR STRUCTURE, AND METHOD FOR THE OPERATION THEREOF

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**Inventor(s):** MAYERHOFER MICHAEL [AT]; DEUTSCHMANN BERND [AT]; FANKHAUSER BERND [AT]

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**Applicant(s):** AUSTRIAMICROSYSTEMS AG UNTERPR [AT]

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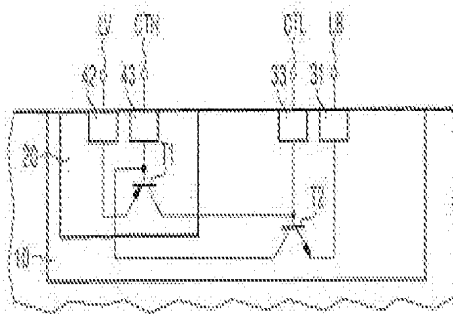
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Disclosed is a protective arrangement for a semiconductor circuit system having a thyristor structure (SCR) which is disposed in a first trough (10) having a first type of conductivity and a second trough (20) that has a second type of conductivity and is embedded in said first trough (10). The first trough encompasses a highly doped region (11; 31) that has the second type of conductivity and is connected to a first potential (VB), and a first control region (13; 33) having the first type of conductivity. The second trough is provided with a highly doped region (22; 42) that has the first type of conductivity and is connected to a second potential (VV), and a second control region (23; 43) having the second type of conductivity. The first and second control region are connected to a first and a second control potential (CTL, CTH), respectively.



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